Taiwan Semiconductor

# 2A, 100V - 200V Surface Mount Ultra Fast Rectifier

#### FEATURES

TAIWAN

Glass passivated junction chip

EMICONDUCTOR

- Ideal for automated placement
- Low profile package
- Ultra fast recovery time for high efficiency
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

## APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Lighting application
- Converter

## **MECHANICAL DATA**

- Case: DO-214AA (SMB)
- Molding compound meets UL 94V-0 flammability rating
- Part no. with suffix "H" means AEC-Q101 qualified
- Packing code with suffix "G" means green compound (halogen-free)
- Moisture sensitivity level: level 1, per J-STD-020
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.09 g (approximately)

KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
I <sub>F(AV)</sub>	2	А		
V <sub>RRM</sub>	100 - 200	V		
I <sub>FSM</sub>	60 A			
T <sub>J MAX</sub>	175 °C			
Package	DO-214AA (SMB)			
Configuration	Single Die			





DO-214AA (SMB)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	SYMBOL	ESH2B	ESH2C	ESH2D	UNIT	
Marking code on the device		ESH2B	ESH2C	ESH2D		
Repetitive peak reverse voltage	V <sub>RRM</sub>	100	150	200	V	
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	70	105	140	V	
Maximum DC blocking voltage	V <sub>DC</sub>	100	150	200	V	
Forward current	I <sub>F(AV)</sub>	2		А		
Surge peak forward current, 8.3 ms single half sine-wave superimposed on rated load per diode	I <sub>FSM</sub>	60			А	
Junction temperature	TJ	- 55 to +175		°C		
Storage temperature	T <sub>STG</sub>	- 55 to +175			°C	



THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-lead thermal resistance	$R_{\Theta JL}$	20	°C/W		
Junction-to-ambient thermal resistance	R <sub>eja</sub>	75	°C/W		

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_A = 25^{\circ}C$ unless otherwise noted)					
PARAMETER	CONDITIONS	SYMBOL	ТҮР	МАХ	UNIT
Forward voltage per diode <sup>(1)</sup>	$I_F = 2A, T_J = 25^{\circ}C$	V <sub>F</sub>	-	0.9	V
Reverse current @ rated $V_R$ per diode <sup>(2)</sup>	$T_J = 25^{\circ}C$	I <sub>R</sub>	-	2	μA
	T <sub>J</sub> = 125°C		-	50	μA
Junction capacitance	1 MHz, V <sub>R</sub> =4.0V	CJ	25	-	pF
	I <sub>F</sub> =0.5A ,I <sub>R</sub> =1.0A	+		20	20
Reverse recovery time	I <sub>RR</sub> =0.25A	t <sub>rr</sub>	-	20	ns

#### Notes:

- 1. Pulse test with PW=0.3 ms
- 2. Pulse test with PW=30 ms

ORDERING INFORMATION						
PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX(*)	PACKAGE	PACKING	
	н	R5	G	SMB	850 / 7" Plastic reel	
ESH2x (Note 1)		R4		SMB	3,000 / 13" Paper reel	
(Note T)		M4		SMB	3,000 / 13" Plastic reel	

#### Note:

1. "x" defines voltage from 100V (ESH2B) to 200V (ESH2D)

\*: Optional available

EXAMPLE P/N					
EXAMPLE P/N	PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX	DESCRIPTION
ESH2DHR5G	ESH2D	Н	R5	G	AEC-Q101 qualified Green compound



## **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)

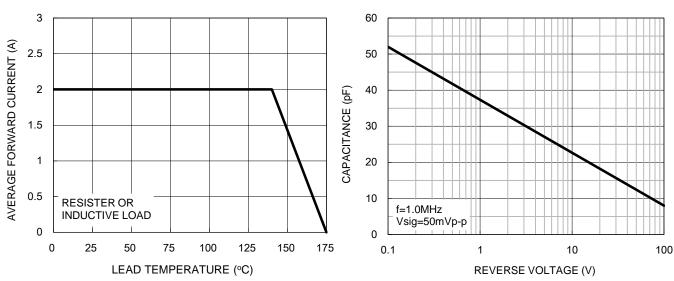
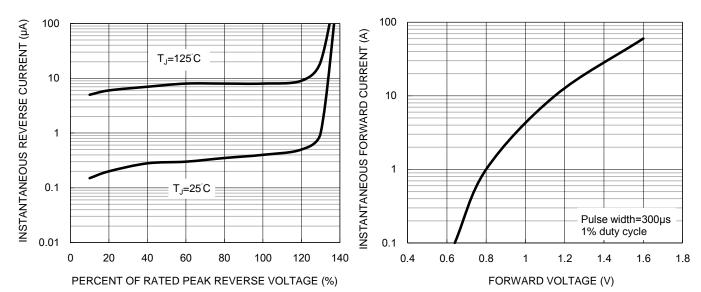


Fig.1 Forward Current Derating Curve

Fig.2 Typical Junction Capacitance

**Fig.3 Typical Reverse Characteristics** 

**Fig.4 Typical Forward Characteristics** 

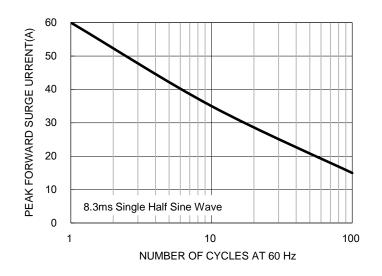




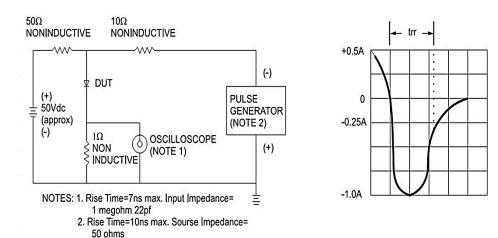
### **CHARACTERISTICS CURVES**

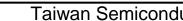
(T<sub>A</sub> = 25°C unless otherwise noted)

#### Fig.5 Maximum Non-repetitive Forward Surge Current



#### Fig.6 Reverse Recovery Time Characteristic And Test Circuit Diagram

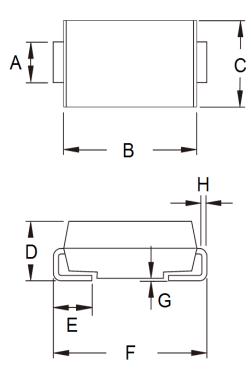






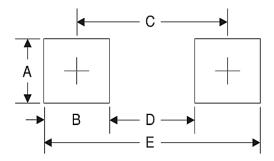
## **PACKAGE OUTLINE DIMENSIONS**

DO-214AA (SMB)



DIM.	Unit (mm)		Unit (inch)	
Divi.	Min	Max	Min	Max
А	1.95	2.20	0.077	0.087
В	4.05	4.60	0.159	0.181
С	3.30	3.95	0.130	0.156
D	1.95	2.65	0.077	0.104
E	0.75	1.60	0.030	0.063
F	5.10	5.60	0.201	0.220
G	0.05	0.20	0.002	0.008
Н	0.15	0.31	0.006	0.012

## SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	2.3	0.091
В	2.5	0.098
С	4.3	0.169
D	1.8	0.071
E	6.8	0.268

### **MARKING DIAGRAM**



P/N

= Marking Code = Green Compound G

YW = Date Code

F = Factory Code



## ESH2B - ESH2D

Taiwan Semiconductor

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